ASSP For Power Supply Applications

Power Management Switch

MB3802

DESCRIPTION

The MB3802 is a power management switch incorporating two switch circuits with extremely low ON resistance.

NO diode is required because the switch block is configured with an N-ch MOS to prevent reverse current at switch OFF.

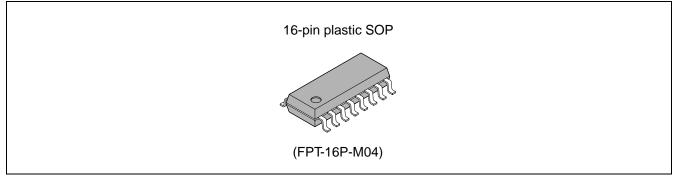
The MB3802 starts at a very low voltage (typical $V_{IN} > 2.2V$) and a stable ON resistance is obtained irrespective of the switching voltage because the internal DC/DC converter applies the optimum voltage for the N-ch MOS gate at switch ON.

Moreover, the load-side capacitor is discharged at switch OFF, and the power supply for various power supply systems is switched efficiently.

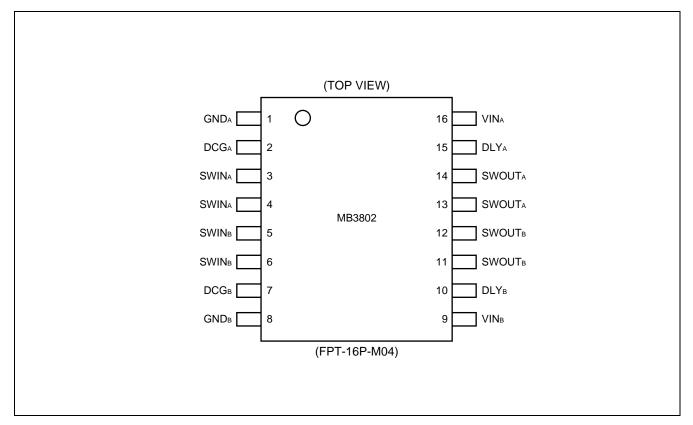
FEATURES

- Extremely low ON resistance:
 - Ron = 0.12 Ω (typical)
 - Ron = 0.06 Ω (typical at parallel connection)
- · Reverse current protection at load side at switch OFF
- Operation start at low input voltage: VIN > 2.2 V (typical)
- Low power consumption At switch OFF: IIN (input voltage) = 0 μ A, VIN = 0 V At switch ON: IIN = 230 μ A, VIN = 5 V
- Load discharge function
- External control of ON/OFF time
- Break-before-make operation



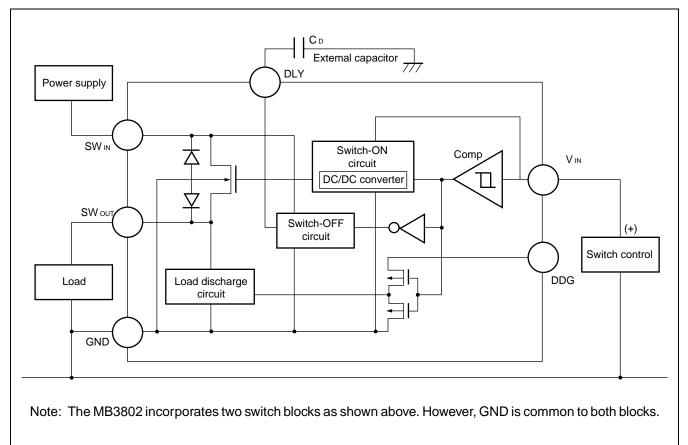


■ PIN ASSIGNMENT



■ PIN DESCRIPTION (SCSI Interface)

Pin No.	Pin symbol	Description		
16	VINA	These pins switch ON at High level and OFF at Low level. They		
9	VINB	serve as power-supply pins for the DC/DC converter to generate the switch gate voltage.		
3, 4	SWINA	Switch Input pins: Two common pins are assigned to SWINA and		
5, 6	SWINB	SWINB. They serve as power-supply pins for the switch-OFF circuit which starts at 1.5V min.		
13, 14	SWOUTA	Switch output pins: Two common pins are assigned to SWOUTA		
11, 12	SWOUTB	and SWOUT _B . When DCGA and DCGB are High level, the load- discharge circuit starts discharge via these pins.		
2	DCGA	SWOUTA/SWOUTB-side discharge control pins: These pins are		
7	DCGB	 used to discharge from the load-side capacitor at switch OFF. Connect them to GND when discharge is not required. 		
15	DLYA	Switch-ON/OFF control pins: The ON/OFF time can be delayed by connecting an external capacitor. Both times are delayed about three fold by installing a 500-pF capacitor between these pins and		
10	DLYB	GND. Leave these pins open when they are not used. 10V may be generated when these pins are open. To keep these pins at high impedance, take care to mount the device so that no current leaks (less than 0.1 μA).		
1	GNDA	Ground pins for input threshold reference voltage and load		
8	GNDB	discharge: When two switching circuits are used, ground both GND pins.		



BLOCK DIAGRAM AND EXTERNAL CONNECTIONS

■ BLOCK DESCRIPTION

The MB3802 is a one-way switching IC with the SWIN and SWOUT pins serving respectively for input and output. When VIN exceeds 2.2 V, the Comp. starts driving the DC/DC converter to switch the N-ch MOS and applies the optimum voltage for the switch gate.

The DC/DC converter boosts the VIN voltage.

When VIN is below 2.1 V, the Comp. stops the DC/DC converter, starts the switch-OFF circuit, and discharges the voltage from the switch gate to GND. The switch-OFF circuit is powered from the SW_{IN} and consumes 0.4μ A at 5 V.

Since the N-ch MOS back gate is connected to GND, switch-OFF reverse current is prevented irrespective of the High level state between SWIN and SWOUT. Note, however, that turning the VIN pin on/off with 1.5 V or less applied to the SWIN pin may cause reverse current to flow because the switch-off circuit does not work then. For the method of compensating for the operation of the switch-off circuit, see section "■APPLICATIONS 7.Low-side Switch."

The load discharge circuit installed between SWout and GND is powered by the DCG pin, and discharges the load-side capacitor at switch OFF. When it is not necessary to discharge the load, connect the DCG pin to GND. The DLY pins are for connection to an external capacitor to delay the switch-ON/OFF time. The surge current at the load side is cut at power-on by controlling the switch-ON time. The switch-ON time depends on the boot time of the DC/DC converter. Consequently, when the VIN level is high and the SWIN level is low, the switch-ON time is small; when the SWIN level is high, the switch-OFF time is small.

■ ABSOLUTE MAXIMUM RATING

				(Ta = +25°C)	
Parameter	Symbol	Condition	Ratings	Unit	
Input Voltage	Vin	—	-0.3 to 7.0	V	
Switching voltage	Marrie	At switch OFF	-0.3 to 7.0	V	
Switching voltage	Vsw	At switch ON	-0.3 to 7.0	v	
Switching current	Isw	At switch-ON peak	3.6	A	
Permissible loss	Po	Ta ≤ + 75°C	290	mW	
Storage Temperature	Тѕтс	—	-55 to +125	°C	

WARNING: Semiconductor devices can be permanently damaged by application of stress (voltage, current, temperature, etc.) in excess of absolute maximum ratings. Do not exceed these ratings.

■ RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Conditions	Ratings			l Init
Falameter			Min.	Typical	Max.	Unit
Input voltage	Vin	—	0	—	6.0	V
Switching level	Vswin	At switch ON	0	—	6.0	V
	VSVVIN	At switch OFF	0	—	6.0	
Switching current	Isw	At switch on (for single switch)	_	_	1.2	A
Gate-pin connection capacitance	Ср		—	—	10	nF
Gate-pin mounting leak current	IDLY	—	-0.1	—	0.1	μΑ
Input voltage to load discharge circuit	Vdcg	VIN = 3V, 5V	2.5	—	6.0	V
Operating temperature	Тор	—	-40	—	+7.5	°C

WARNING: The recommended operating conditions are required in order to ensure the normal operation of the semiconductor device. All of the device's electrical characteristics are warranted when the device is operated within these ranges.

Always use semiconductor devices within their recommended operating condition ranges. Operation outside these ranges may adversely affect reliability and could result in device failure.

No warranty is made with respect to uses, operating conditions, or combinations not represented on the data sheet. Users considering application outside the listed conditions are advised to contact their FUJITSU representatives beforehand.

■ ELECTRICAL CHARACTERISTICS

1. DC Characteristics

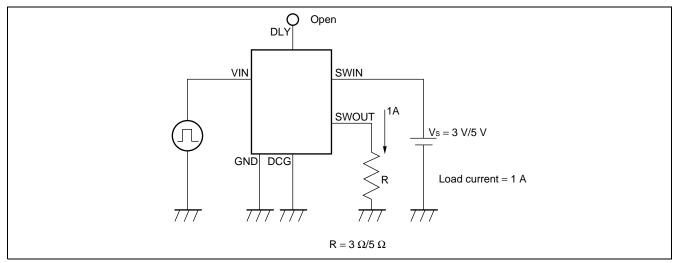
					(Ta	a = +25°C
Parameter	Symbol	Condition	Ratings			Unit
Faianleter			Min	Тур	Max	Unit
	lin1	VIN = 0 V	_	0		μA
Input current		VIN = 3 V	_	100	200	μA
	lin2	VIN = 5 V	—	230	460	μA
Swiching resistance	Ron1	VIN = 3 V, ISW = 0.5 A, VSWIN = 3 V	_	120	160	mΩ
	Ron2	VIN = 5 V, ISW = 0.5 A, VSWIN = 3 V	_	130	175	mΩ
Switch-OFF leak current	١L	VIN = 0 V, VSWIN = 6 V	_	0.5	2.0	μA
	Vth1	At switch ON	2.0	2.2	2.4	V
Input threshold voltage	Vth2	At switch OFF	1.9	2.1	2.3	V
Input hysteresis width	VHYS	—	50	100	_	mV
Switch resistance	Ron	VIN = 3 V, 5 V, Isw = 0.5 A Ta = -40°C to +75°C	_		210	mΩ
Switch charge resistance	RDCG1	VSWOUT = 3 V, VDCG = 3 V	_	750	1500	Ω
	RDCG2	VSWOUT = 5 V, VDCG = 5 V	_	500	1000	Ω
Input voltage to switch charge circuit	IDCG	VDCG = 5 V	_	0	2	μΑ

2. AC Characteristics

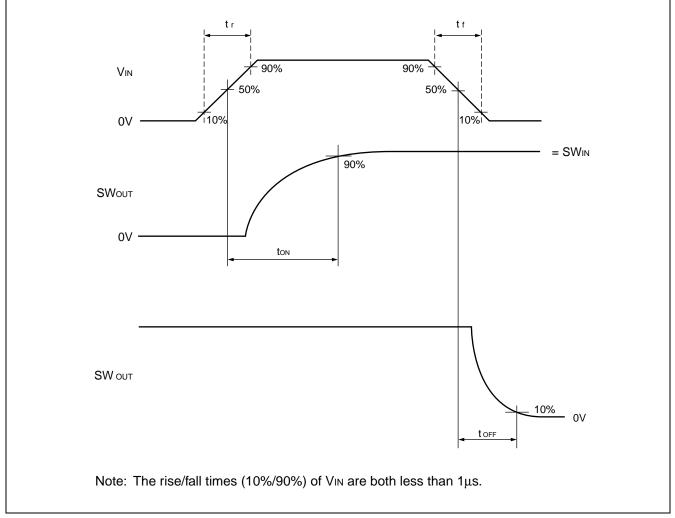
(Ta = +25°C) Ratings Parameter Symbol Condition Unit Min Max Тур $V_{IN} = 0V \rightarrow 3V$, $V_{SWIN} = 3V$ 300 900 ton1 20 μs Switch-ON time $V_{IN} = 0V \rightarrow 5V$, $V_{SWIN} = 5V$ 20 150 450 ton2 μs $V_{IN} = 3V \rightarrow 0V$, $V_{SWIN} = 3V$ toff1 5 60 180 μs Switch OFF time $V_{IN} = 5V \rightarrow 0V$, $V_{SWIN} = 5V$ 5 toff2 30 150 μs $V_{IN} = 3V / 0V$, $V_{SWIN} = 3V$ tHYS1 10 240 720 μs Switch ON/OFF time lag $V_{IN} = 5V / 0V$, $V_{SWIN} = 5V$ tHYS2 10 120 300 μs

■ AC CHARACTERISTIC TEST DIAGRAMS

1. Test Condition

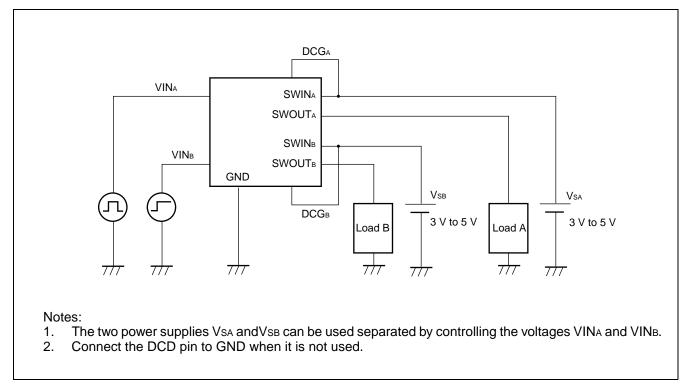


2. Switch-ON/OFF Timing Chart

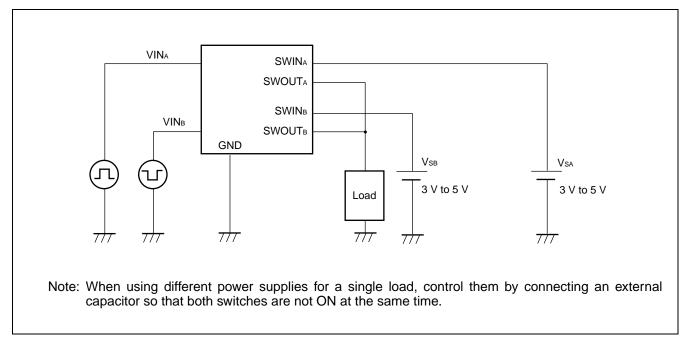


■ APPLICATIONS

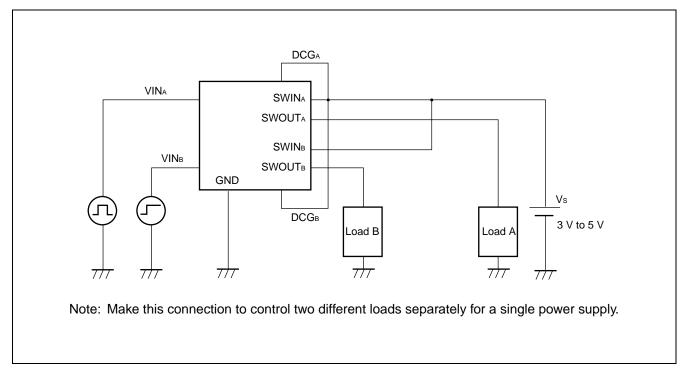
1. Separate Use of Two Switching Circuits



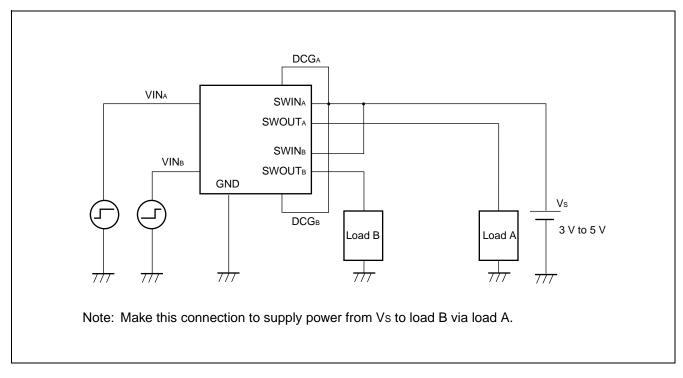
2. Switching Two Power Supplies



3. Switching Two Loads

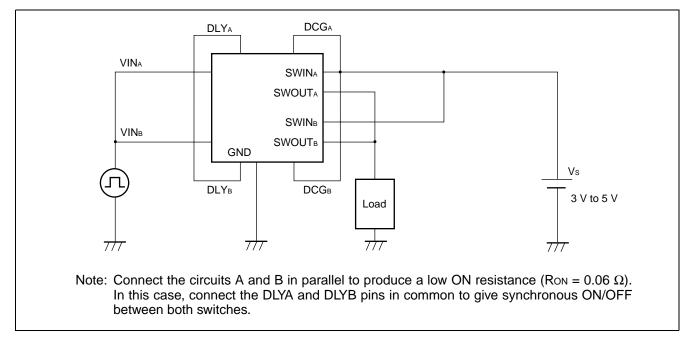


4. Connecting Serial Switches

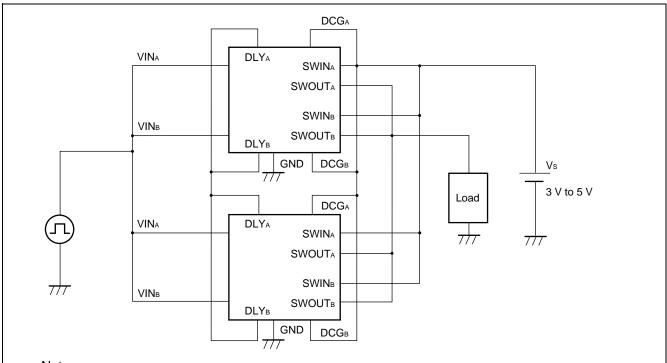




5. Connecting Parallel Switches



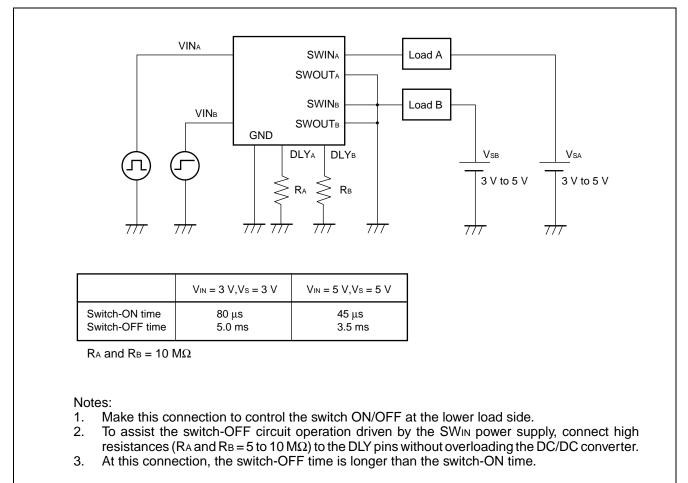
6. 25% ON Resistance

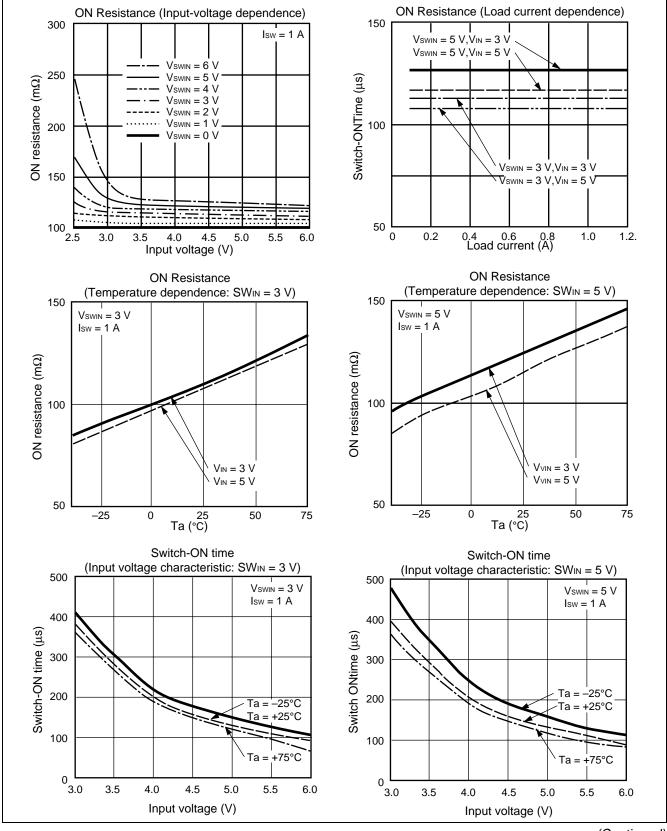


Notes:

- 1. Make this connection to produce an ON resistance that is much lower than the above connection. Also, connect the DLY pins in common.
- 2. Consider the difference between the ON resistances and the switch-ON/OFF times between two devices (MB3802) and insure that load control is not offset at one device.

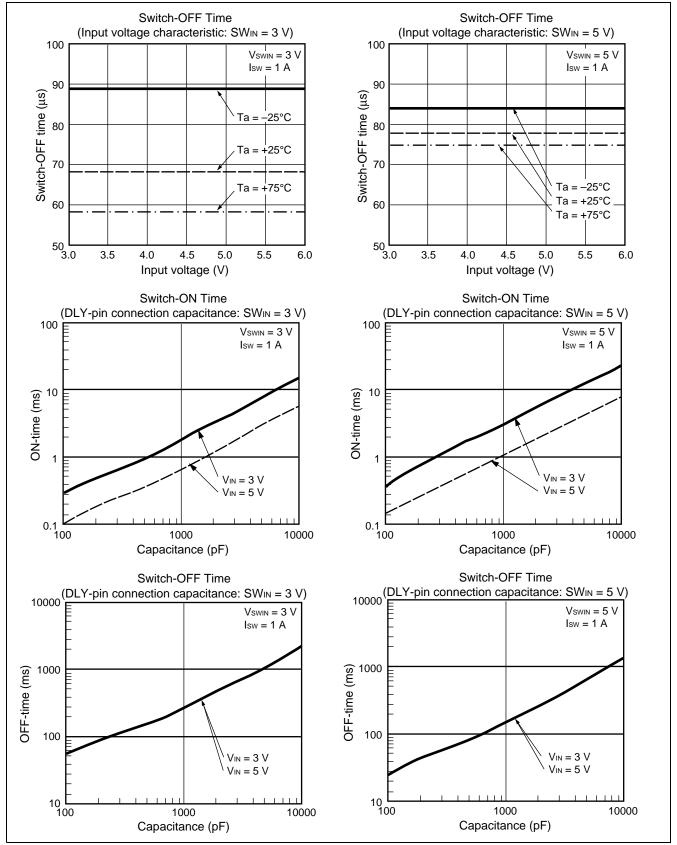
7. Low-side Switch





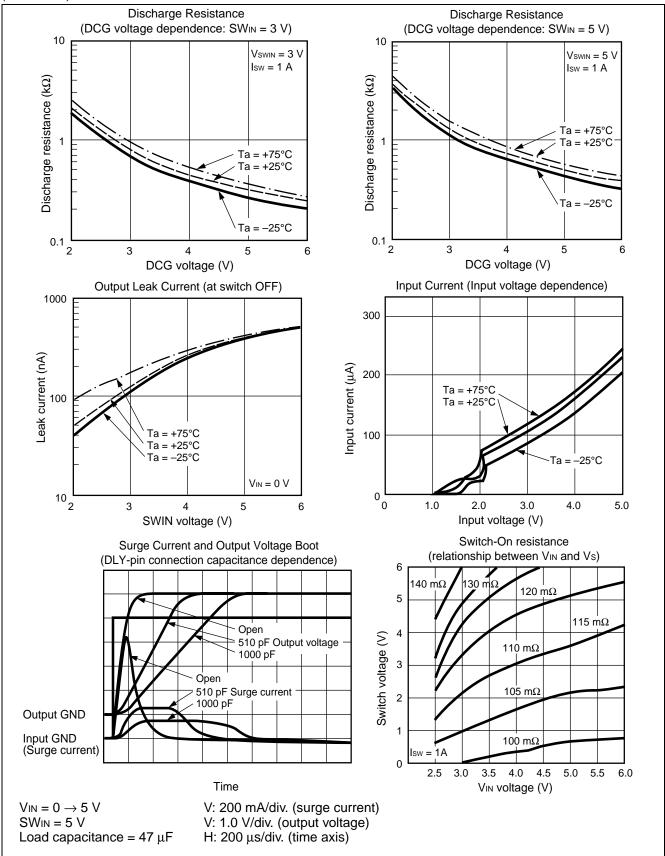
■ TYPICAL PERFORMANCE CHARACTERISTICS

(Continued)

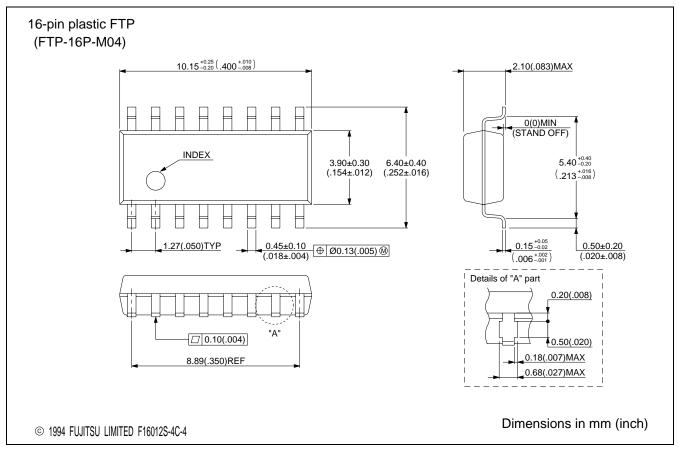


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